TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOS V-H)

# **TPCA8031-H**

High-Efficiency DC-DC Converter Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: QSW = 5.0 nC (typ.)
- Low drain-source ON-resistance: RDS (ON) = 7.3 m $\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 60 \text{ S (typ.)}$
- Low leakage current:  $I_{DSS} = 10 \mu A (max) (V_{DS} = 30 V)$
- Enhancement mode:  $V_{th} = 1.5 \text{ to } 2.5 \text{ V (V}_{DS} = 10 \text{ V, I}_{D} = 1 \text{ mA})$

### Absolute Maximum Ratings (Ta = 25°C)

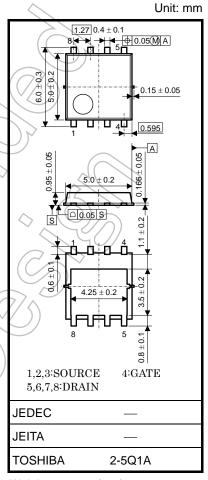
Characteristic		Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	30	V	
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		V <sub>DGR</sub>	30	V	
Gate-source voltage		V <sub>GSS</sub>	±20		
Drain current	DC (Note 1)	ID	24	A	
	Pulsed (Note 1)	IDP	72	^	
Drain power dissipation	on (Tc=25°C)	(PD	30	//w	
Drain power dissipation	on $(t = 10 s)$ (Note 2a)	PD	2.8	W.	
Drain power dissipation (t = 10 s) (Note 2b)		PD	1,6	W	
Single-pulse avalanche energy (Note 3)		EAS	75	mJ	
Avalanche current		I <sub>AR</sub>	24	Α	
Repetitive avalanche energy (Tc = 25°C) (Note 4)		EAR	3.0	mJ	
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C	

Note: For Notes 1 to 4, refer to the next page.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the

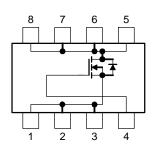
reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.069 g (typ.)

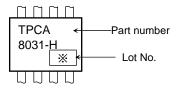
### **Circuit Configuration**



#### **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case $(Tc = 25^{\circ}C)$	R <sub>th (ch-c)</sub>	4.17	°C/W
Thermal resistance, channel to ambient $(t=10 \; s) \eqno(Note \; 2a)$	R <sub>th (ch-a)</sub>	44.6	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	78.1	°C/W

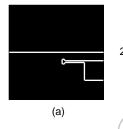
### Marking (Note 5)



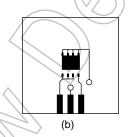
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)



FR-4 25.4 × 25.4 × 0.8 (Unit: mm)



 $\begin{aligned} & \text{FR-4} \\ 25.4 \times 25.4 \times 0.8 \\ & \text{(Unit: mm)} \end{aligned}$ 

Note 3:  $V_{DD} = 24 \text{ V}$ ,  $T_{ch} = 25 ^{\circ}\text{C}$  (initial),  $L = 100 \ \mu \text{ H}$ ,  $R_G \neq 25 \ \Omega$ ,  $I_{AR} = 24 \ A$ 

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: \* Weekly code: (Three digits)

Week of manufacture

(01) for the first week of the year, continuing up to 52 or 53)

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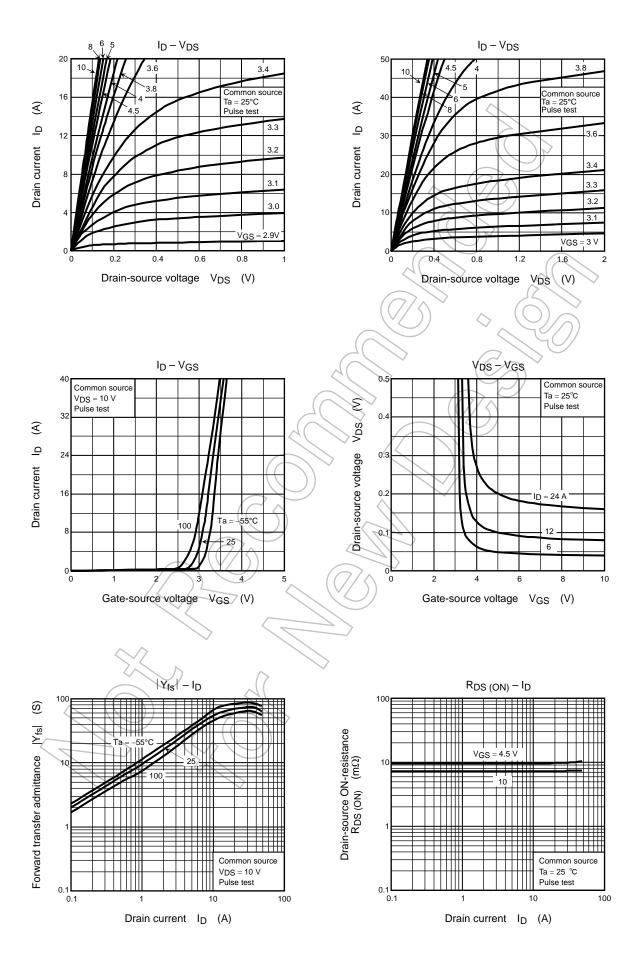
Year of manufacture (The last digit of the year)

## **Electrical Characteristics (Ta = 25°C)**

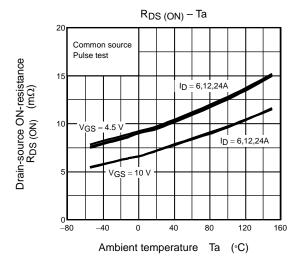
Ch	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cur	rent	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA	
Drain cutoff curre	ent	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V		_	10	μА	
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_	_	V	
		V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15	_	_		
Gate threshold vo	oltage	$V_{th}$	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	1.5	) /_	2.5	V	
Drain-source ON-resistance		_	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 12 A	) <u> </u>	9.6	13.4	<b>m</b> 0	
		R <sub>DS</sub> (ON)	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 12 A	$\mathcal{D}$	7.3	11.0	mΩ	
Forward transfer	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 12 A	30	60	_	S	
Input capacitance		C <sub>iss</sub>		_	1433	2150		
Reverse transfer	capacitance	C <sub>rss</sub>	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	83	125	pF	
Output capacitance		C <sub>oss</sub>			303	$\nearrow$		
Gate resistance		Rg	$V_{DS} = 10 \text{ V}, V_{GS} \neq 0 \text{ V}, f = 5 \text{ MHz}$	-6	3.4	5.1	Ω	
Switching time	Rise time	t <sub>r</sub>	V <sub>GS</sub> 10 V   I <sub>D</sub> = 12 A   V <sub>OUT</sub>   C <sub>G</sub>   C		3.4	) —		
	Turn-on time	t <sub>on</sub>			9.6	_	ns	
	Fall time	t <sub>f</sub>	G. Y. W. W. O. B. C. T. L.		9.9	_	IIS	
	Turn-off time	t <sub>off</sub>	V <sub>DD</sub> ≈ 15 V Duty ≤ 1%, t <sub>w</sub> = 10 μs		33	_		
Total gate charge (gate-source plus gate-drain)		Qg	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 24 \text{ A}$	_	21	_		
			V <sub>DD</sub> ≈ 24 V, V <sub>GS</sub> = 5 V, I <sub>D</sub> = 24 A		11			
Gate-source char	rge 1	Q <sub>gs1</sub>		_	4.7		nC	
Gate-drain ("Miller") charge		$Q_{gd}$	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 24 \text{ A}$	_	3.0	_		
Gate switch charge		Q <sub>SW</sub>		_	5.0	_		

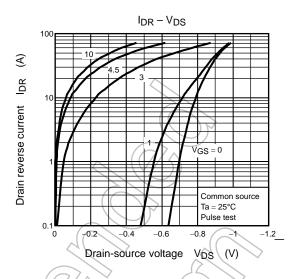
## Source-Drain Ratings and Characteristics (Ta = 25°C)

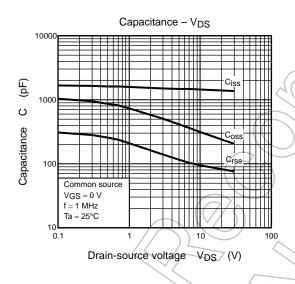
Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Drain reverse current Pulse (Note 1)	I <sub>DRP</sub>	<u> </u>	_	_	72	Α
Forward voltage (diode)	VDSF	I <sub>DR</sub> = 24 A, V <sub>GS</sub> = 0 V	_	_	-1.2	V

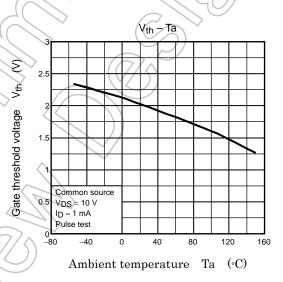


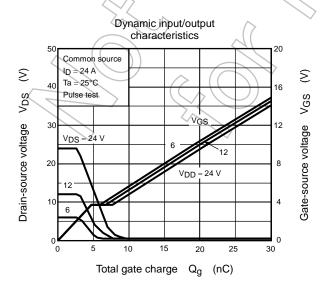
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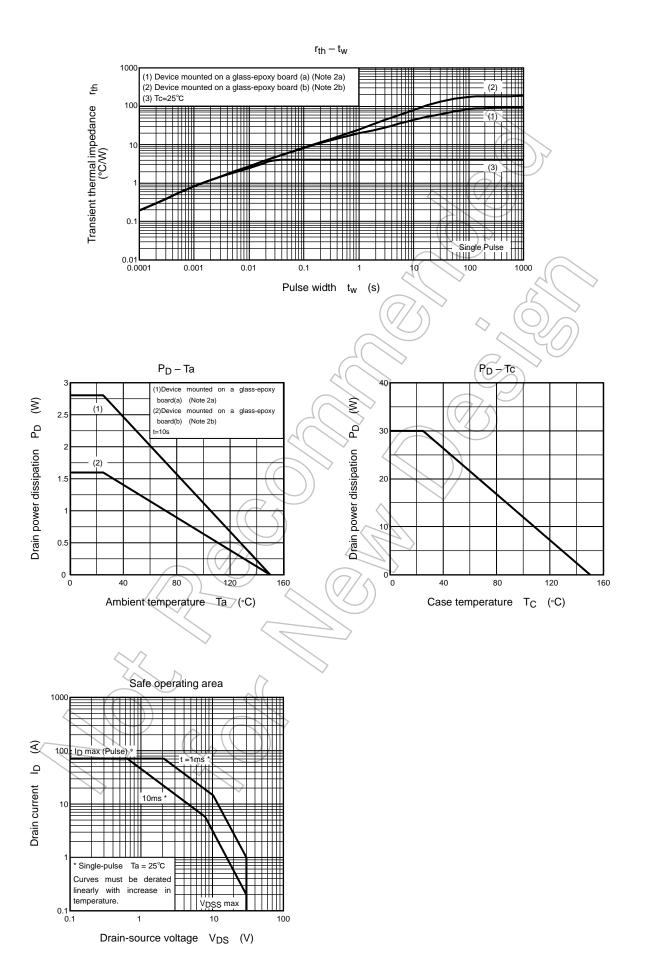








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